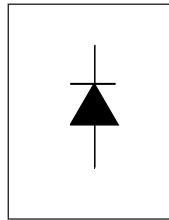


International  
**IOR** Rectifier

**QUIETIR** Series  
8EWF..S

**SURFACE MOUNTABLE  
FAST SOFT RECOVERY  
DIODE**



$V_F < 1.3V @ 8A$   
 $t_{rr} = 80ns$   
 $V_{RRM} 1000 \text{ to } 1200V$

**Description/Features**

The 8EWF..S fast soft recovery **QUIETIR** rectifier series has been optimized for combined short reverse recovery time, low forward voltage drop and low leakage current

The glass passivation ensures stable reliable operation in the most severe temperature and power cycling conditions.

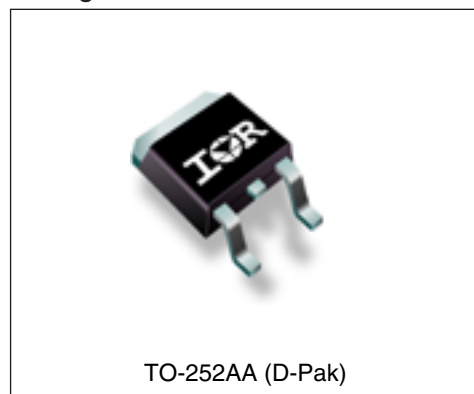
Typical applications are both:

- Output rectification and freewheeling diode in inverters, choppers and converters.
- Input rectifications where severe restrictions on conducted EMI should be met.

**Major Ratings and Characteristics**

Characteristics	8EWF..S	Units
$I_{F(AV)}$ Sinusoidal waveform	8	A
$V_{RRM}$	1000to1200	V
$I_{FSM}$	170	A
$V_F @ 8A, T_J=25^\circ C$	1.3	V
$t_{rr} @ 1A, 100A/\mu s$	80	ns
$T_J$ range	-40to150	$^\circ C$

**Package Outline**



Voltage Ratings

Part Number	$V_{RRM}$ , maximum peak reverse voltage V	$V_{RSM}$ , maximum non repetitive peak reverse voltage V	$I_{RRM}$ 150°C mA
8EWF10S	1000	1100	4
8EWF12S	1200	1300	

Absolute Maximum Ratings

Parameters	8EWF..S	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current	8	A	@ $T_C = 94^\circ\text{C}$ , 180° conduction half sine wave
$I_{FSM}$ Max. Peak One Cycle Non-Repetitive Surge Current	170	A	10ms Sine pulse, rated $V_{RRM}$ applied
	200		10ms Sine pulse, no voltage reapplied
$I^2t$ Max. $I^2t$ for fusing	144	$A^2s$	10ms Sine pulse, rated $V_{RRM}$ applied
	200		10ms Sine pulse, no voltage reapplied
$I^2\sqrt{t}$ Max. $I^2\sqrt{t}$ for fusing	2000	$A^2/\sqrt{s}$	$t = 0.1$ to 10ms, no voltage reapplied

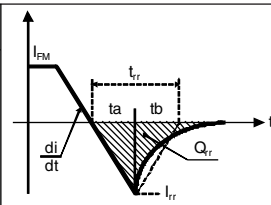
Electrical Specifications

Parameters	8EWF..S	Units	Conditions
$V_{FM}$ Max. Forward Voltage Drop	1.3	V	@ 8A, $T_J = 25^\circ\text{C}$
$r_t$ Forward slope resistance	25.6	$m\Omega$	$T_J = 150^\circ\text{C}$
$V_{F(TO)}$ Threshold voltage	0.93	V	
$I_{RM}$ Max. Reverse Leakage Current	0.1	mA	$T_J = 25^\circ\text{C}$
	4		$T_J = 150^\circ\text{C}$

$V_R = \text{rated } V_{RRM}$

Typical Reverse Recovery Characteristics

Parameters	8EWF..S	Units	Conditions
$t_{rr}$ Reverse Recovery Time	270	ns	$I_F @ 8A_{pk}$ @ $25A/\mu s$ @ $T_J = 25^\circ\text{C}$
$I_{rr}$ Reverse Recovery Current	4.2	A	
$Q_{rr}$ Reverse Recovery Charge	1	$\mu C$	
S Typical Snap Factor	$t_b/t_a$	-	



**Thermal-Mechanical Specifications**

Parameters	8EWF..S	Units	Conditions
T <sub>J</sub> Max. Junction Temperature Range	-40 to 150	°C	
T <sub>stg</sub> Max. Storage Temperature Range	-40 to 150	°C	
	Soldering Temperature	240	°C for 10 seconds
R <sub>thJC</sub> Max. Thermal Resistance Junction to Case	2.5	°C/W	DC operation
R <sub>thJA</sub> Typ. Thermal Resistance Junction to Ambient (PCB Mount)**	50	°C/W	
wt Approximate Weight	1(0.03)	g(oz.)	
T Case Style	TO-252AA(D-Pak)		

\*\*When mounted on 1" square (650mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz (140µm) copper 40°C/W  
 For recommended footprint and soldering techniques refer to application note #AN-994

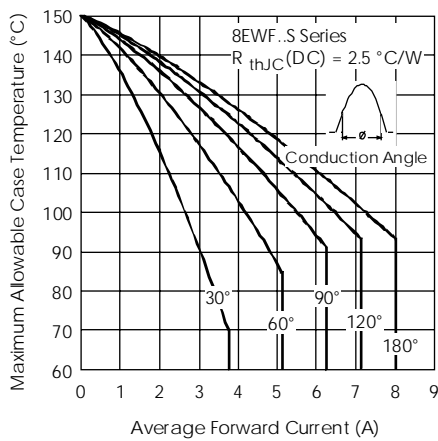


Fig. 1 - Current Rating Characteristics

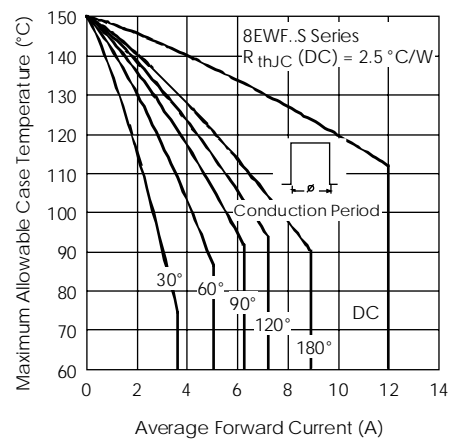


Fig. 2 - Current Rating Characteristics

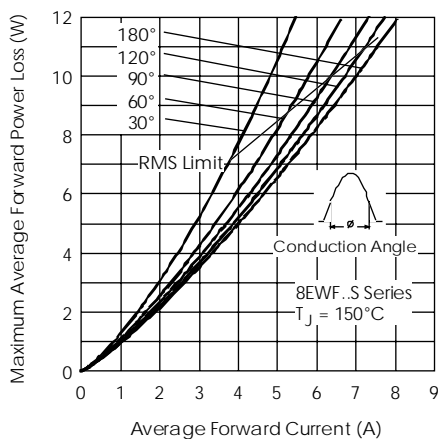


Fig. 3 - Forward Power Loss Characteristics

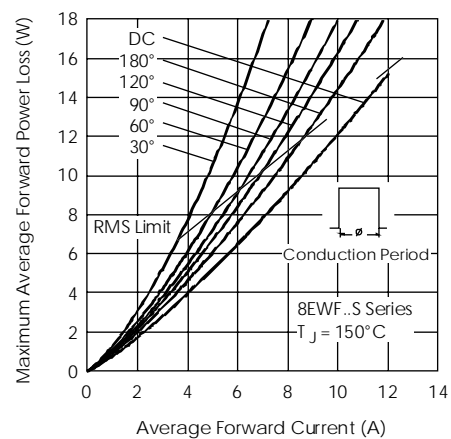


Fig. 4 - Forward Power Loss Characteristics

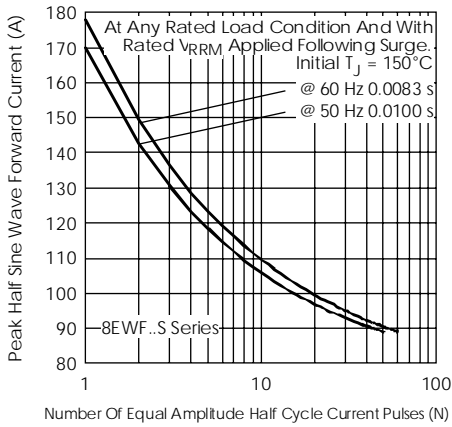


Fig.5-Maximum Non-Repetitive Surge Current

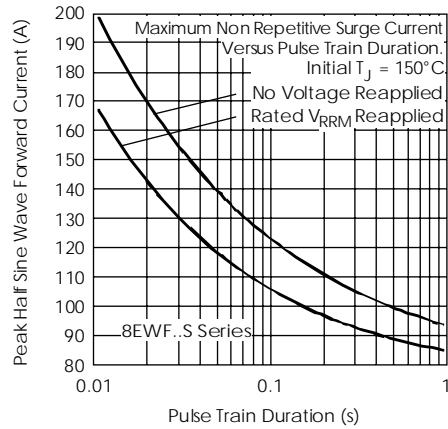


Fig.6-Maximum Non-Repetitive Surge Current

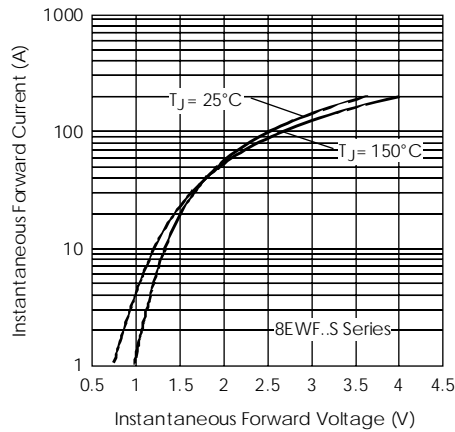


Fig.7-Forward Voltage Drop Characteristics

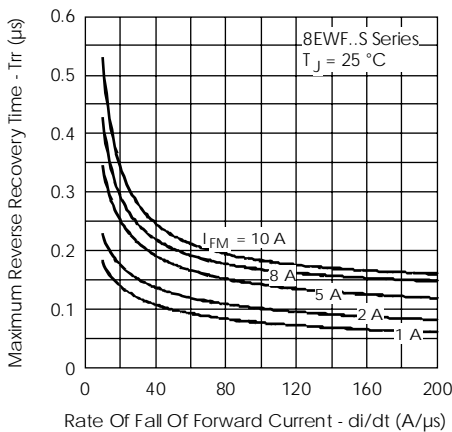


Fig.8-Recovery Time Characteristics,  $T_J = 25^\circ\text{C}$

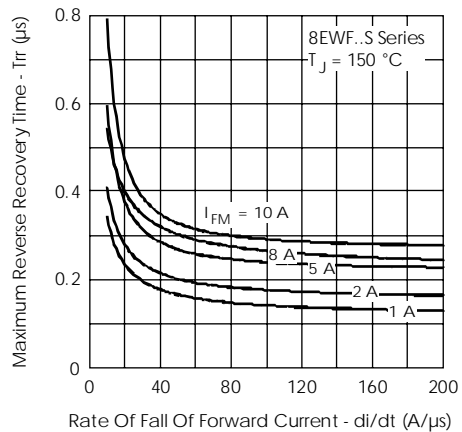


Fig.9-Recovery Time Characteristics,  $T_J = 150^\circ\text{C}$

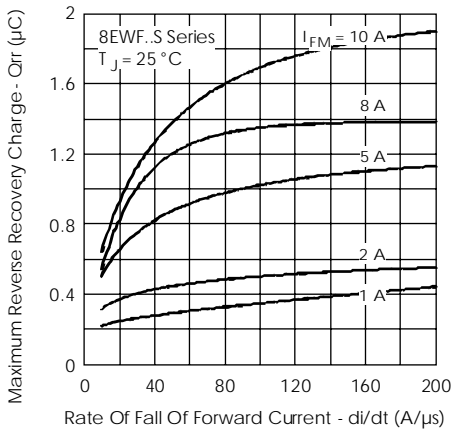


Fig. 10-Recovery Charge Characteristics, T<sub>J</sub>=25°C

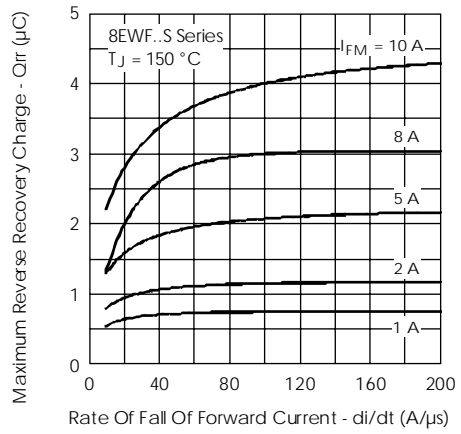


Fig. 11-Recovery Charge Characteristics, T<sub>J</sub>=150°C

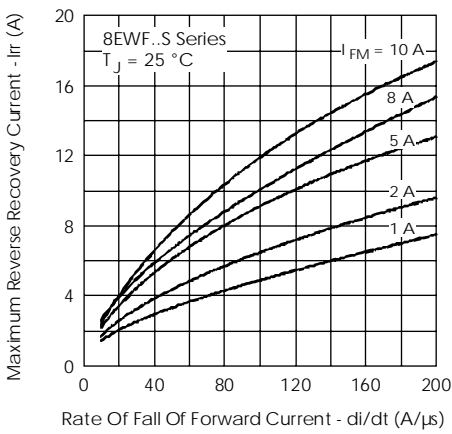


Fig. 12-Recovery Current Characteristics, T<sub>J</sub>=25°C

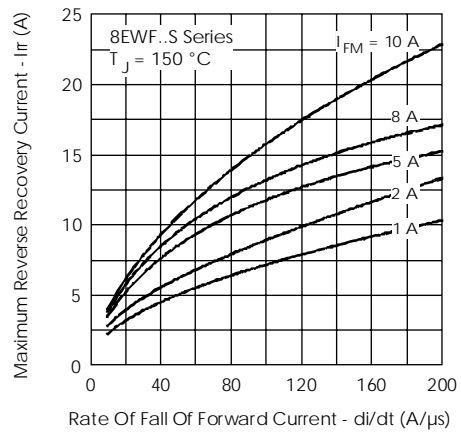


Fig. 13-Recovery Current Characteristics, T<sub>J</sub>=150°C

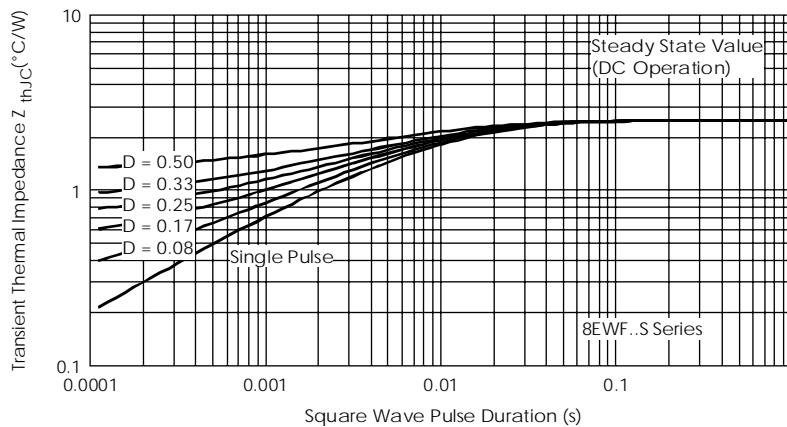


Fig. 14-Thermal Impedance Z<sub>thJC</sub> Characteristics

Ordering Information Table

Device Code						
8	E	W	F	12	S	TRL
①	②	③	④	⑤	⑥	⑦

<p><b>1</b> - Current Rating</p> <p><b>2</b> - Circuit Configuration: E = Single Diode</p> <p><b>3</b> - Package: W = D-Pak</p> <p><b>4</b> - Type of Silicon: F = Fast Soft Recovery Rectifier</p> <p><b>5</b> - Voltage code: Code x 100 = <math>V_{RRM}</math></p> <p><b>6</b> - S = Surface Mountable</p> <p><b>7</b> - Tape and Reel Option: TRL = Left Orientation Reel TRR = Right Orientation Reel</p>	<table border="1" style="margin-left: auto; margin-right: auto;"> <tr> <td>10 = 1000V</td> </tr> <tr> <td>12 = 1200V</td> </tr> </table>	10 = 1000V	12 = 1200V
10 = 1000V			
12 = 1200V			

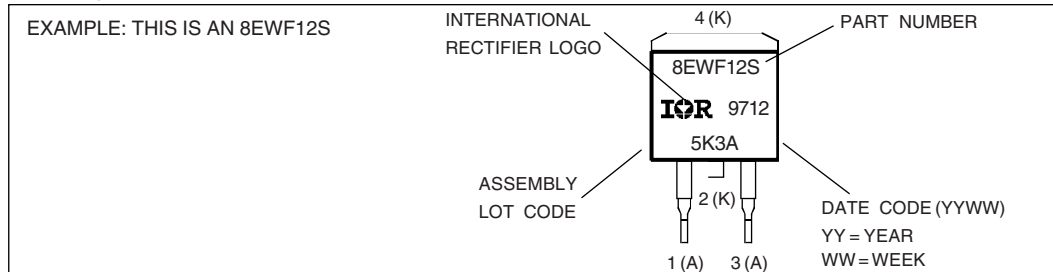
Outline Table

MINIMUM RECOMMENDED FOOTPRINT

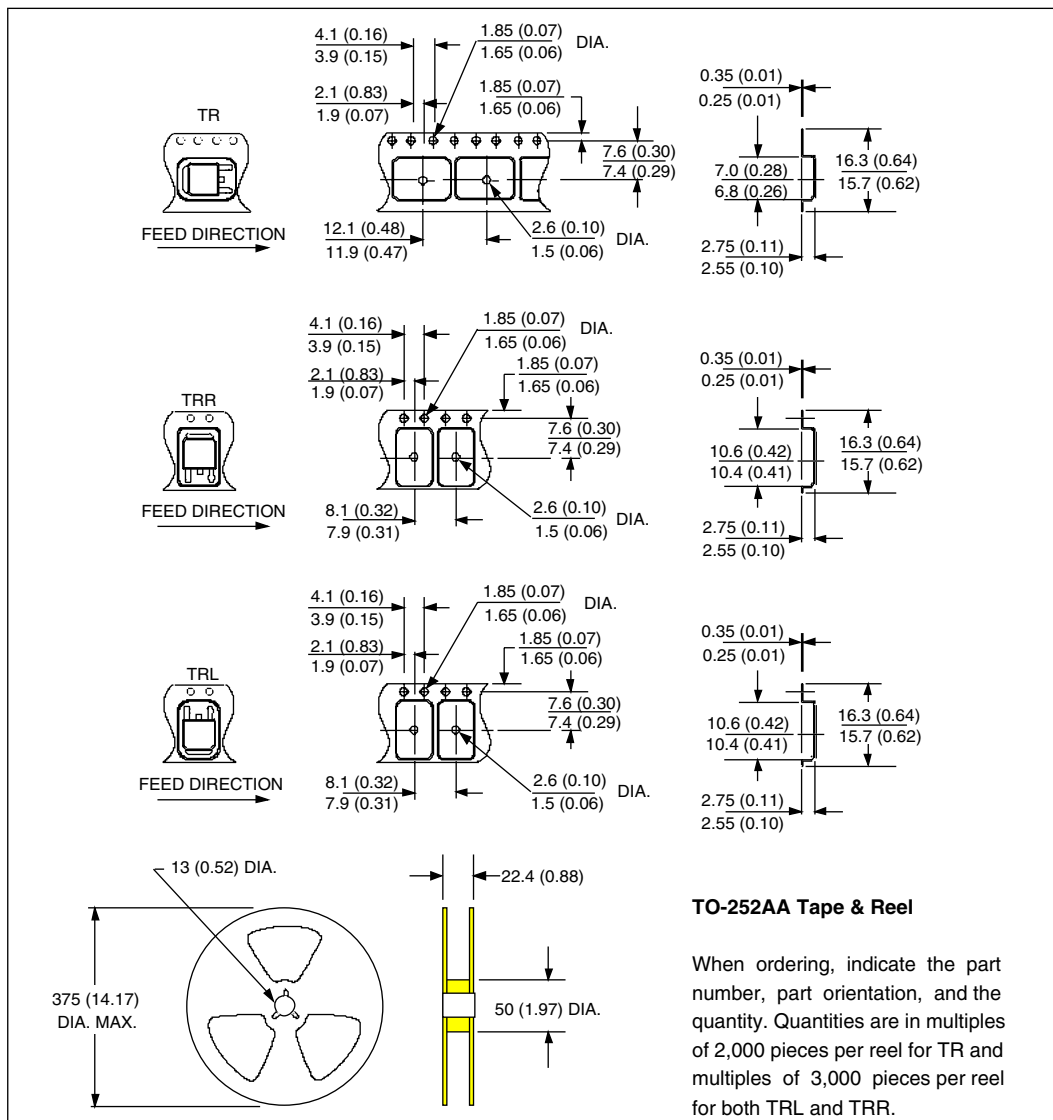
1 - Anode  
2 - Cathode  
3 - Anode  
4 - Cathode

Dimensions in millimeters and (inches)

Marking Information



Tape & Reel Information



**WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245 U.S.A. Tel: (310) 322 3331. Fax: (310) 322 3332.  
**EUROPEAN HEADQUARTERS:** Hurst Green, Oxted, Surrey RH8 9BB, U.K. Tel: ++ 44 1883 732020. Fax: ++ 44 1883 733408.  
**IR CANADA:** 15 Lincoln Court, Brampton, Markham, Ontario L6T3Z2. Tel: (905) 453 2200. Fax: (905) 475 8801.  
**IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg. Tel: ++ 49 6172 96590. Fax: ++ 49 6172 965933.  
**IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino. Tel: ++ 39 11 4510111. Fax: ++ 39 11 4510220.  
**IR FAR EAST:** K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo, Japan 171. Tel: 81 3 3983 0086.  
**IR SOUTHEAST ASIA:** 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994. Tel: ++ 65 838 4630.  
**IR TAIWAN:** 16 Fl. Suite D.207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan. Tel: 886 2 2377 9936.